

Surface Mount Ultrafast Power Rectifiers

..ldeally suited for high voltage high frequency rectification, or as free wheeling and protection diodes in surface mount applications where compact size and weight are critical to the system.

- * Low Power Loss, High efficiency
- * Glass Passivated chips junction
- * 150 Operating Junction Temperature
- * Low Stored Charge Majority Carrier Conduction
- *Low Forward Voltage Drop , High Current Capability
- * High-Switching Speed 35 & 50 Nanosecond Recovery Time
- * Small Compact Surface Mountable Package with J-Bend Lead
- * Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O







MAXIMUM RATINGS

Characteristic	Symbol	MU						l lm is
Characteristic		31	32	33	34	35	36	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM} \ V_{RWM} \ V_{R}$	50	100	150	200	300	400	٧
RMS Reverse Voltage	V _{R(RMS)}	35	70	105	140	210	280	٧
Average Rectifier Forward Current	Io	3.0			Α			
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware, single phase, 60Hz)	I _{FSM}	75		50		А		
Operating and Storage Junction Temperature Range	T_J , T_stg	-65 to +125						

ELECTRIAL CHARACTERISTICS

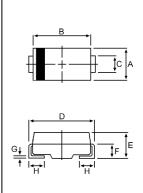
Characteristic	Symbol	MU						11
Characteristic		31	32	33	34	35	36	Unit
	V_{F}	0.95		1.30		٧		
Maximum Instantaneous Reverse Current (Rated DC Voltage, T _C = 25) (Rated DC Voltage, T _C = 125)	I _R	5.0 70					uA	
everse Recovery Time ($I_F = 0.5 \text{ A}, I_R = 1.0, I_{rr} = 0.25 \text{ A}$)			50		ns			
Typical Junction Capacitance (Reverse Voltage of 4 volts & f=1 MHz)	C _P	55		45		₽F		

ULTRAFAST RECTIFIERS

3.0 AMPERES 50-400 VOLTS



DO-214AA(SMB)

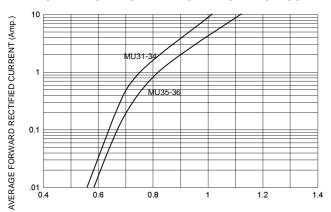


DIM	MILLIMETERS				
ווועו	MIN	MAX			
Α	3.30	3.90			
В	4.20	4.60			
С	1.80	2.20			
D	5.10	5.60			
Е	1.90	2.50			
F		1.30			
G		0.22			
Н	0.95	1.35			

CASE---Transfer molded plastic

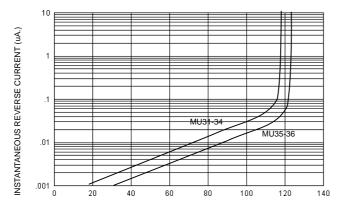
OLARITY---Cathode indicated polarity band

FIG-1 TYPICAL FORWARD CHARACTERISITICS

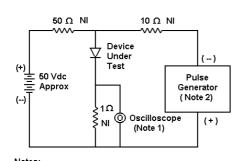


FORWARD VOLTAGE (Volts)

FIG-2 TYPICAL REVERSE CHARACTERISTICS



PERCENT OF PEAK REVERSE VOLTAGE (%)



Notes: 1. Rise Time = 7 ns max. Input Impedance =1 M Ω , 22 pF 2. Rise Time = 10 ns max. Input Impedance = 50 Ω

FIG-3 FORWARD CURRENT DERATING CURVE

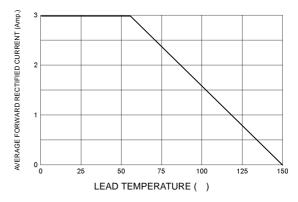


FIG-4TYPICAL JUNCTION CAPACITANCE

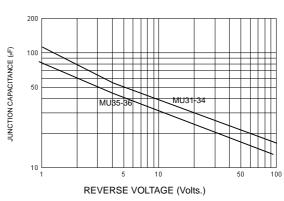
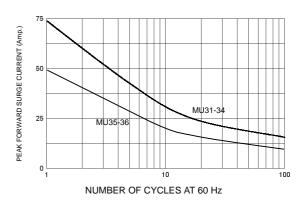


FIG-5PEAK FORWARD SURGE CURRENT



-0.25A

Set time base for 10/20 ns/cm

FIG-6 Reverse Recovery Time Characteristic and Test Circuit Diagram



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